

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / STANDARD

PART NUMBER: 20GL2C41A

MANUFACTURER: TOSHIBA

REMARK: TC=80C

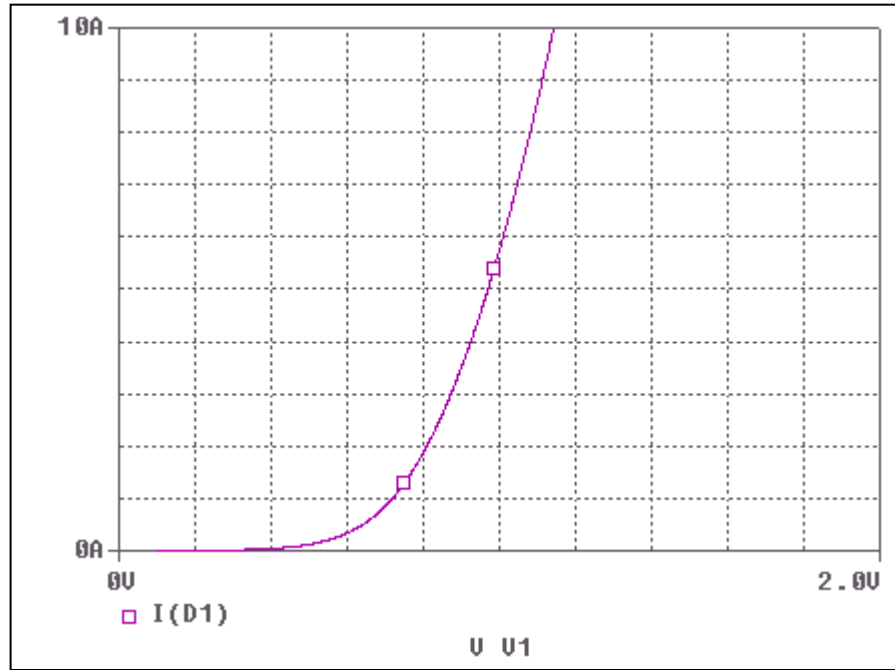


Bee Technologies Inc.

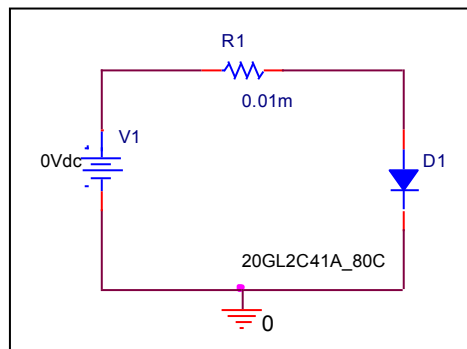
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

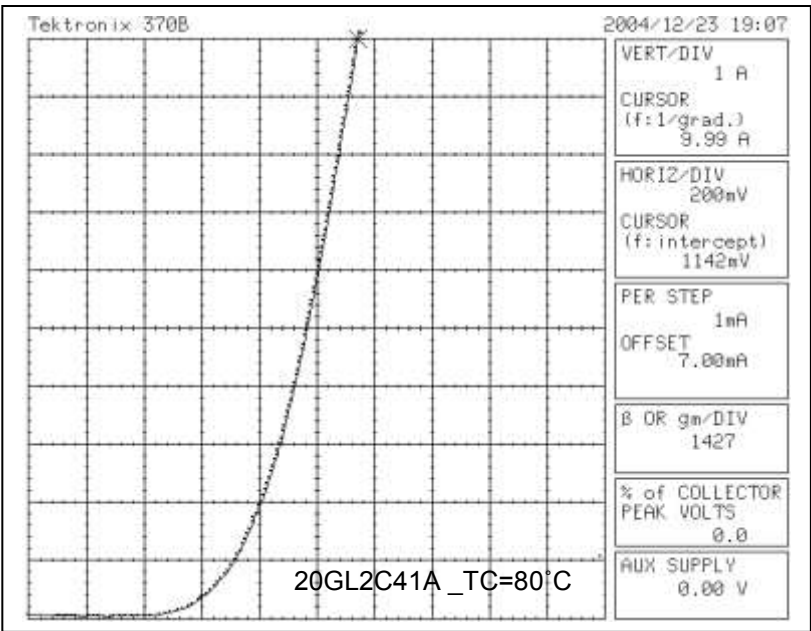


Evaluation Circuit



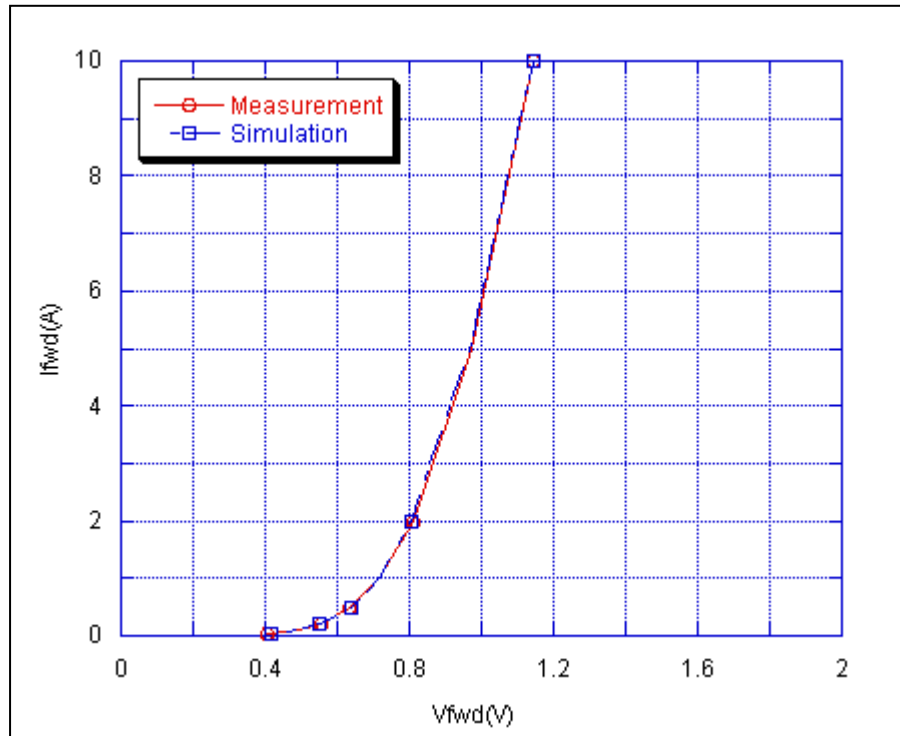
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

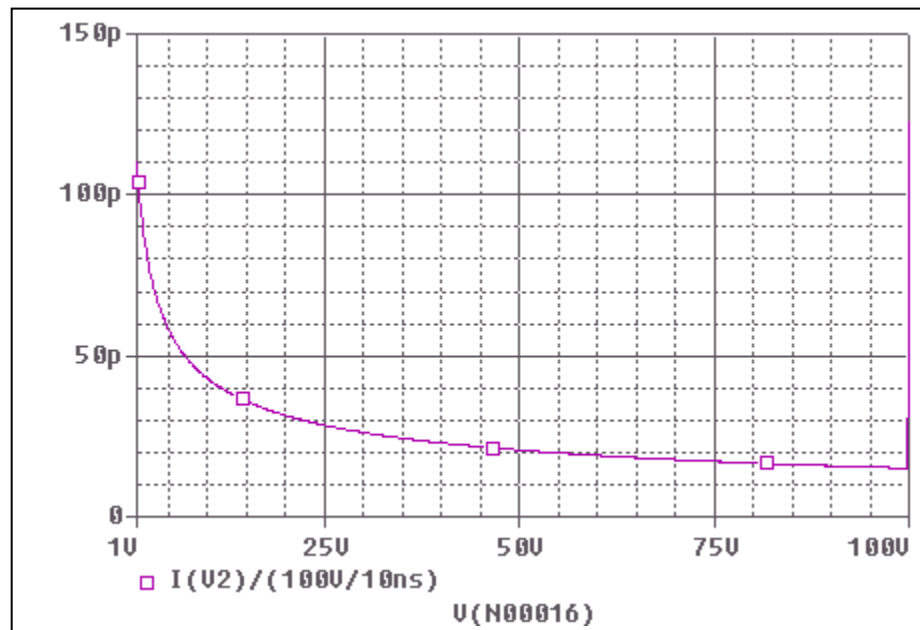


Simulation Result

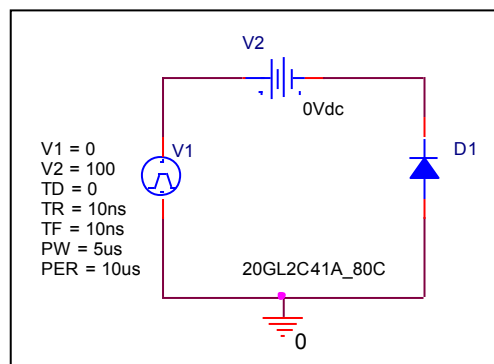
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.05	0.406	0.417	-2.709
0.1	0.494	0.481	2.632
0.2	0.556	0.548	1.439
0.5	0.632	0.640	-1.266
1	0.716	0.718	-0.279
2	0.810	0.808	0.247
5	0.970	0.969	0.103
10	1.142	1.140	0.175

Capacitance Characteristic

Circuit Simulation Result

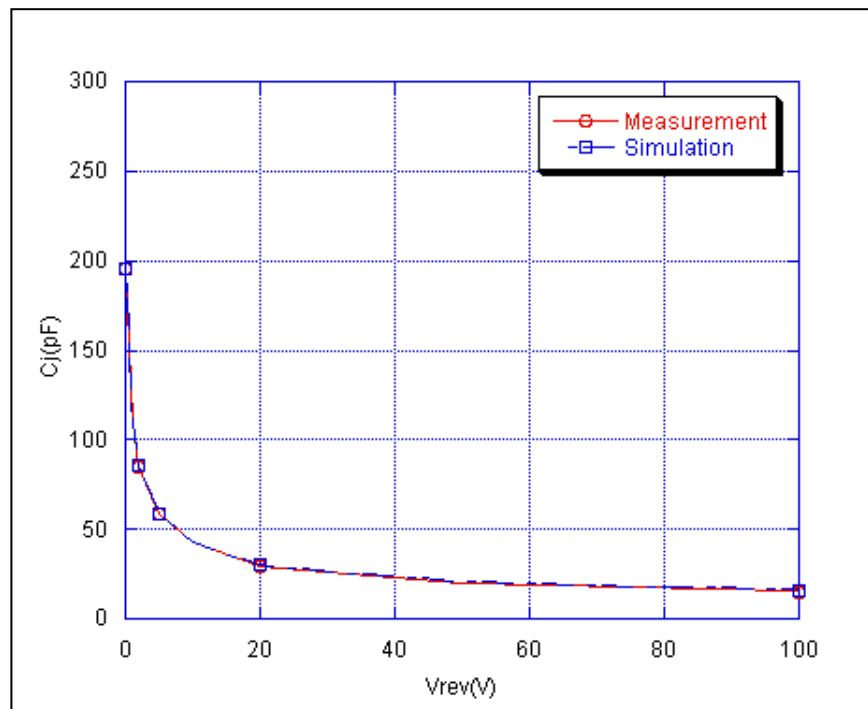


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

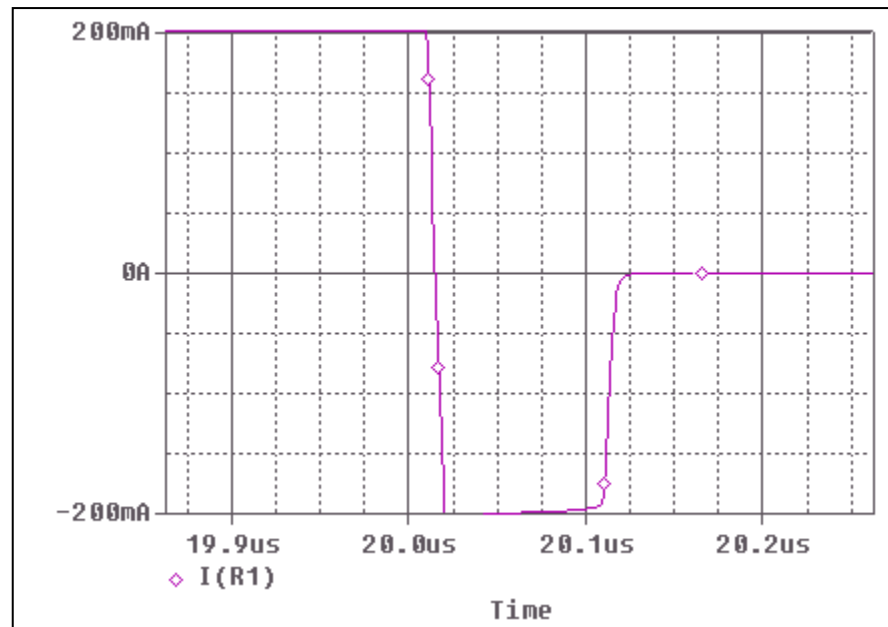


Simulation Result

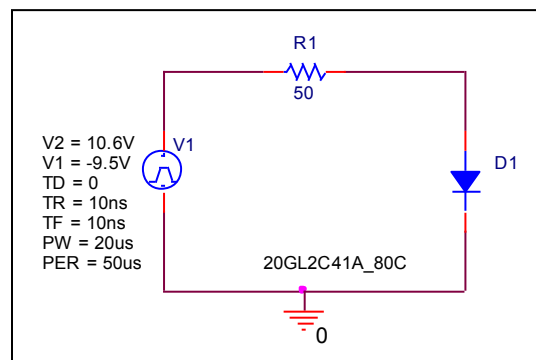
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	195.790	195.790	0.000
1	109.310	109.970	-0.604
2	85.050	85.350	-0.353
5	58.590	58.420	0.290
10	42.780	43.030	-0.584
20	29.490	30.490	-3.391
50	20.070	20.730	-3.288
100	15.110	15.580	-3.111

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

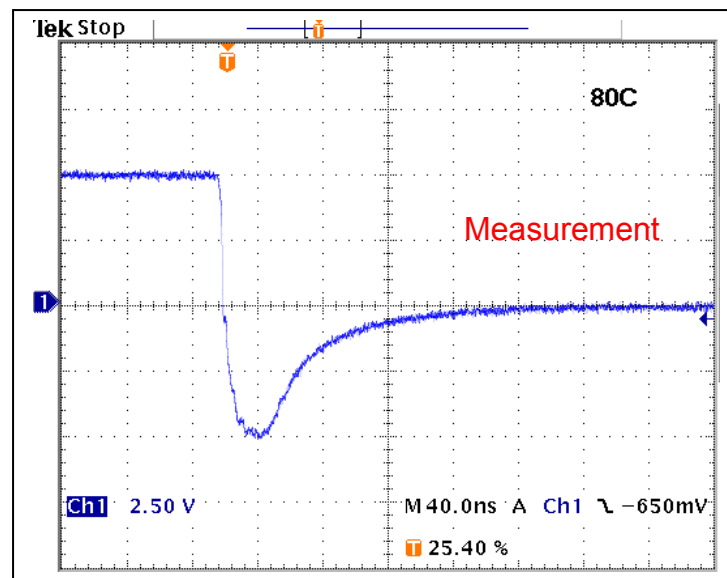


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	100.8	ns	101.8	ns	0.992

Reverse Recovery Characteristic

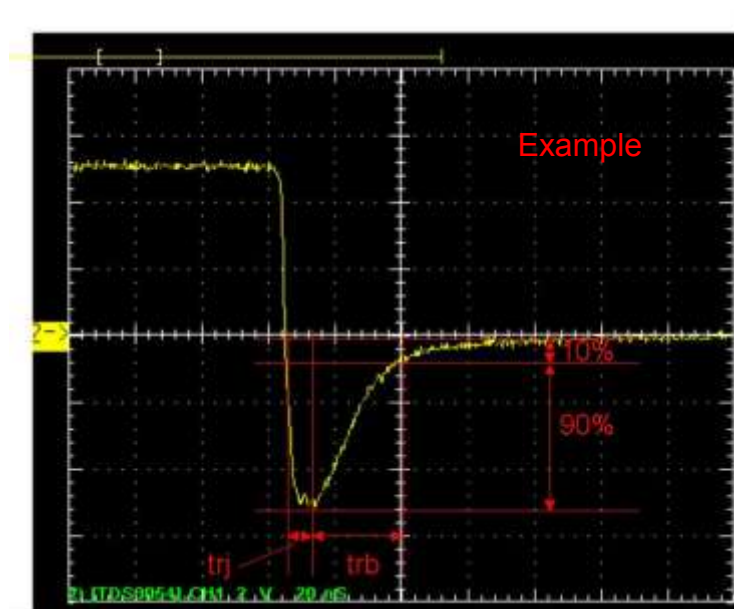
Reference



$T_{rj} = 20.8(\text{ns})$

$T_{rb} = 80(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.02(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}